

Silicon NPN Power Transistors

2SC3179

DESCRIPTION

- With TO-220 package
- Complement to type 2SA1262
- Low collector saturation voltage

APPLICATIONS

- Audio and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

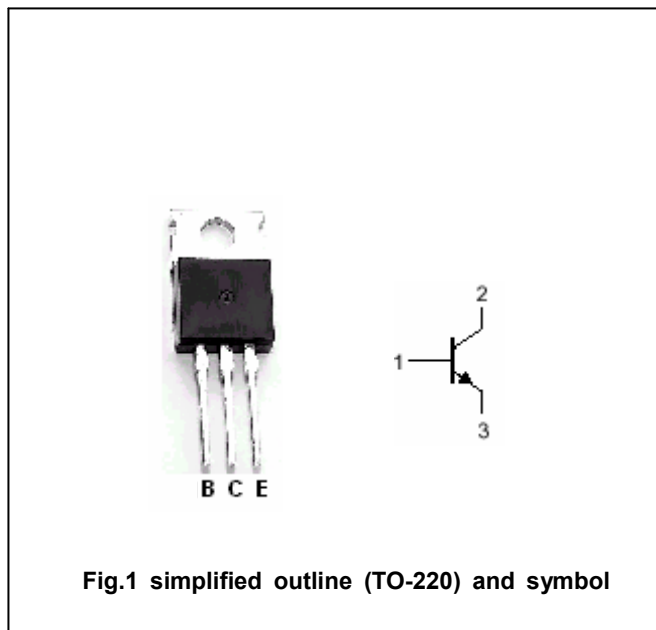


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	80	V
V _{CEO}	Collector-emitter voltage	Open base	60	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		4	A
I _B	Base current		1	A
P _C	Collector power dissipation	T _C =25°C	30	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA, I _B =0	60			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =2A; I _B =0.2 A			0.6	V
I _{CBO}	Collector cut-off current	V _{CB} =80V; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			100	μA
h _{FE}	DC current gain	I _C =1A; V _{CE} =4V	40			
f _T	Transition frequency	I _E =-0.2A; V _{CE} =12V		15		MHz
C _{OB}	Output capacitance	f=1MHz; V _{CB} =10V		60		pF

Switching times resistive load

t _{on}	Turn-on time	I _C =2A I _{B1} =-I _{B2} =0.2A R _L =10Ω; V _{CC} =20V		0.2		μs
t _s	Storage time			1.9		μs
t _f	Fall time			0.29		μs

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PACKAGE OUTLINE

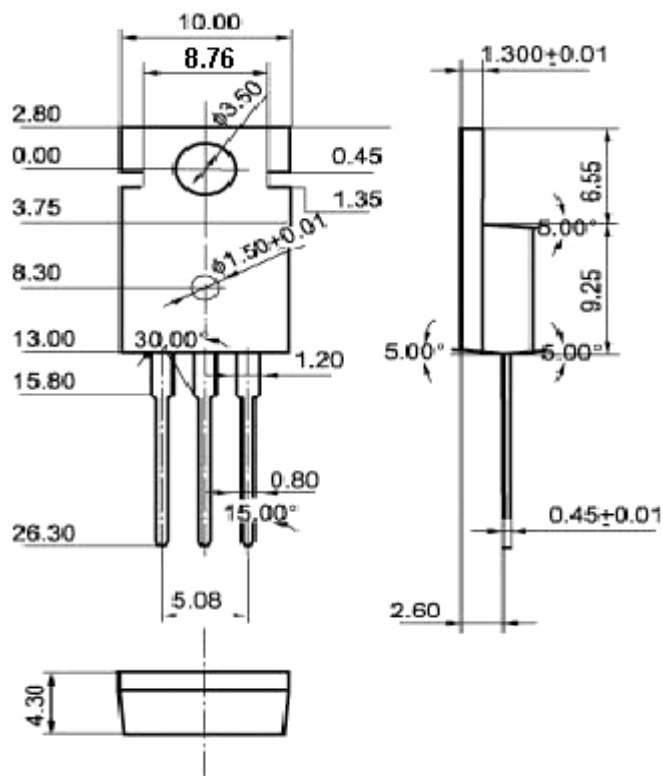


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)